Title: Monte Carlo simulation of GaAs(001) surface smoothing in equilibrium conditions

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- Kinetics of GaAs(001) surface smoothing in equilibrium conditions is simulated.
- The stages of step-terraced morphology formation are elucidated.
- Monatomic step length and mean island size kinetics are compared with experiment.
- The role of atom migration through the gas phase to smoothing is considered.
- Diffusion activation, lateral bond and adatom desorption energies are estimated.